

R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



| R-C VALUES FOR TANK CONFIGURATION | | | |
|--|-----------|------------|------|
| Thermal Resistance (°C/W) | | | |
| Junction to | Ambient | Case | Foot |
| RT1 | 15.6312 | 43.9707 m | N/A |
| RT2 | 40.8698 | 1.2169 | N/A |
| RT3 | 21.7919 | 321.0293 m | N/A |
| RT4 | 6.7071 | 1.1181 | N/A |
| Thermal Capacitance (Joules/°C) | | | |
| Junction to | Ambient | Case | Foot |
| CT1 | 72.2258 m | 24.4063 m | N/A |
| CT2 | 1.9882 | 1.2080 m | N/A |
| CT3 | 1.3539 | 2.1222 | N/A |
| CT4 | 6.7570 m | 12.5919 m | N/A |

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

| Thermal Resistance ($^{\circ}\text{C}/\text{W}$) | | | |
|--|------------|------------|------|
| Junction to | Ambient | Case | Foot |
| RF1 | 7.1626 | 1.5045 | N/A |
| RF2 | 14.4537 | 123.6809 m | N/A |
| RF3 | 15.8360 | 819.1907 m | N/A |
| RF4 | 47.5477 | 252.6284 m | N/A |
| Thermal Capacitance (Joules/ $^{\circ}\text{C}$) | | | |
| Junction to | Ambient | Case | Foot |
| CF1 | 5.4167 m | 1.0552 m | N/A |
| CF2 | 49.2744 m | 14.4672 m | N/A |
| CF3 | 358.5101 m | 2.9659 m | N/A |
| CF4 | 902.0871 m | 3.5436 | N/A |

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

